

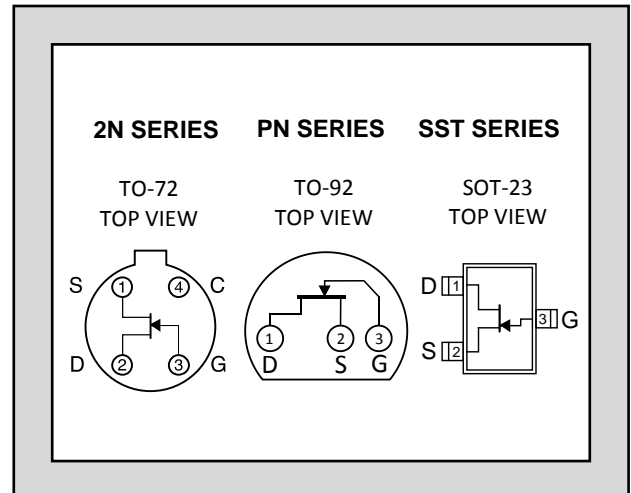
LINEAR SYSTEMS

Over Three Decades of Quality Through Innovation

2N/PN/SST 4117, 4118, 4119

ULTRA-HIGH INPUT IMPEDANCE
N-CHANNEL JFET AMPLIFIER

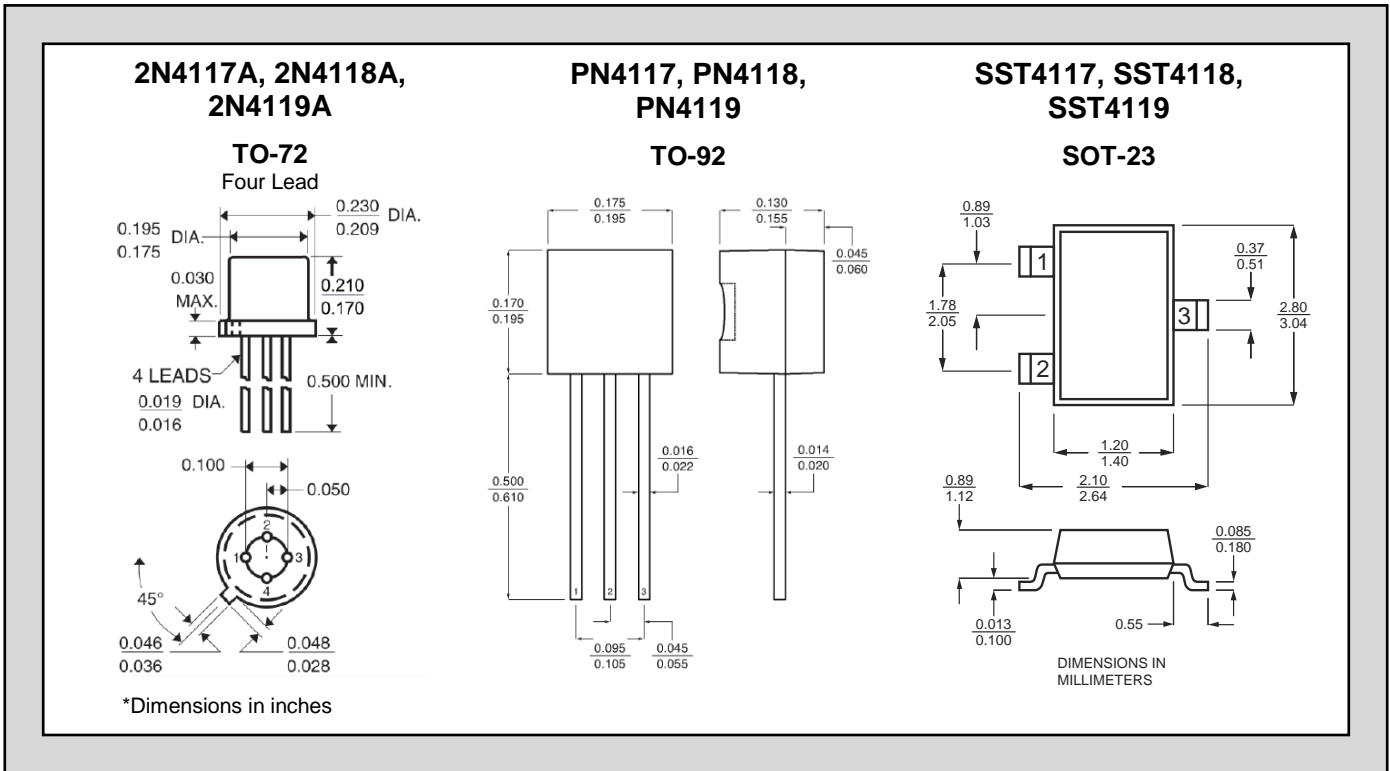
FEATURES	
LOW POWER	$I_{DSS} < 600 \mu A$ (2N4117A)
MINIMUM CIRCUIT LOADING	$I_{GSS} < 1 \text{ pA}$ (2N4117A Series)
ABSOLUTE MAXIMUM RATINGS (NOTE 3) @ 25°C (unless otherwise noted)	
Gate-Source or Gate-Drain Voltage	-40V
Gate-Current	50mA
Total Device Dissipation (Derate 2mW/°C above 25°C)	300mW
Storage Temperature Range	-55°C to +150°C
Lead Temperature (1/16" from case for 10 seconds)	300°C



ELECTRICAL CHARACTERISTICS @ 25°C (unless otherwise noted)

SYMBOL	CHARACTERISTIC	4117		4118		4119		UNITS	CONDITIONS	
		MIN	MAX	MIN	MAX	MIN	MAX			
BV_{GSS}	Gate-Source Breakdown Voltage	-40	--	-40	--	-40	--	V	$I_G = -1 \mu A$ $V_{DS} = 0$	
$V_{GS(off)}$	Gate-Source Cutoff Voltage	-0.6	-1.8	-1	-3	-2	-6		$V_{DS} = 10V$ $I_D = 1nA$	
I_{DSS}	Saturation Drain Current (NOTE 2)	0.03	0.60	0.08	0.60	0.20	0.80	mA	$V_{DS} = 10V$ $V_{GS} = 0$	
I_{GSS}	Gate Reverse Current 2N4117A, 2N4118A, 2N4119A	--	-1	--	-1	--	-1	pA	$V_{GS} = -20V$ $V_{DS} = 0$	150°C
		--	-2.5	--	-2.5	--	-2.5	nA		
	PN4117, PN4118, PN4119 SST4117, SST4118, SST4119	--	-10	--	-10	--	-10	pA	$V_{GS} = -10V$ $V_{DS} = 0$	150°C
		--	-25	--	-25	--	-25	nA		
g_{fs}	Common-Source Forward Transconductance	70	450	80	650	100	700	μS	$V_{DS} = 10V$ $V_{GS} = 0$	f=1kHz
g_{os}	Common-Source Output Conductance	--	3	--	5	--	10			
C_{iss}	Common-Source Input Capacitance (NOTE 4)	--	3	--	3	--	3	pF	$V_{DS} = 10V$ $V_{GS} = 0$	f=1MHz
C_{rss}	Common-Source Reverse Transfer Capacitance (NOTE 4)	--	1.5	--	1.5	--	1.5			

STANDARD PACKAGE DIMENSIONS:



NOTES:

1. Due to symmetrical geometry, these units may be operated with source and drain leads interchanged.
2. This parameter is measured during a 2 ms interval 100 ms after power is applied. (Not a JEDEC condition.)
3. Absolute maximum ratings are limiting values above which serviceability may be impaired.
4. Not production tested, guaranteed by design.

Information furnished by Linear Integrated Systems is believed to be accurate and reliable. However, no responsibility is assumed for its use; nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent rights of Linear Integrated Systems.

Linear Integrated Systems (LIS), established in 1987, is a third-generation precision semiconductor company providing high-quality discrete components. Expertise brought to LIS is based on processes and products developed at Amelco, Union Carbide, Intersil and Micro Power Systems by company Founder John H. Hall. Hall, a protégé of Silicon Valley legend Dr. Jean Hoerni, was the director of IC Development at Union Carbide, Co-Founder and Vice President of R&D at Intersil, and Founder/President of Micro Power Systems.